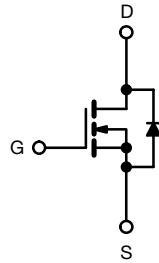
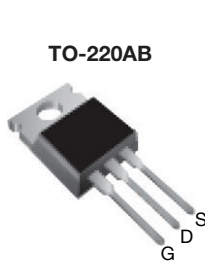


## Power MOSFET



N-Channel MOSFET

### FEATURES

- Low gate charge  $Q_g$  results in simple drive requirement
- Improved gate, avalanche, and dynamic  $dV/dt$  ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Low  $R_{DS(on)}$
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching
- Hard switched and high frequency circuits

### PRODUCT SUMMARY

$V_{DS}$ (V)	500	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.21
$Q_g$ max. (nC)	110	
$Q_{gs}$ (nC)	33	
$Q_{gd}$ (nC)	54	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFB20N50KPbF
	SiHFB20N50K-E3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	500	V	
Gate-source voltage	$V_{GS}$	$\pm 30$		
Continuous drain current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A	
		$T_C = 100\text{ }^\circ\text{C}$		
Pulsed drain current <sup>a</sup>	$I_{DM}$	80		
Linear derating factor		2.2	$W/^\circ\text{C}$	
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	330	mJ	
Repetitive avalanche current <sup>a</sup>	$I_{AR}$	20	A	
Repetitive avalanche energy <sup>a</sup>	$E_{AR}$	28	mJ	
Maximum power dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	280	W
Peak diode recovery $dV/dt$ <sup>c</sup>	$dV/dt$	10	V/ns	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$	
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s	300		
Mounting torque	6-32 or M3 screw	10	N	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 1.6\text{ mH}$ ,  $R_g = 25\text{ }^\circ\Omega$ ,  $I_{AS} = 20\text{ A}$
- $I_{SD} \leq 20\text{ A}$ ,  $dI/dt \leq 350\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	58	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.45	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
= 25 °C,	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.61	-	V/°C	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V	
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	50	$\mu\text{A}$	
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 12\text{ A}^b$	-	0.21	0.25	$\Omega$	
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 12\text{ A}$	11	-	-	S	
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$	-	2870	-	pF	
Output capacitance	$C_{oss}$		-	320	-		
Reverse transfer capacitance	$C_{rss}$		-	34	-		
Output capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	3480	-	
Effective output capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	85	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 0\text{ V to } 400\text{ V}$	-	160	-	
Gate-source charge	$Q_{gs}$		$I_D = 20\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 <sup>b</sup>	-	-	110	nC
Gate-drain charge	$Q_{gd}$			-	-	33	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 20\text{ A}$ $R_g = 7.5\text{ }\Omega, V_{GS} = 10\text{ V}, \text{ see fig. 10}^b$	-	22	-	ns	
Rise time	$t_r$		-	74	-		
Turn-off delay time	$t_{d(off)}$		-	45	-		
Fall time	$t_f$		-	33	-		
Gate input resistance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$	0.3	-	2.9	$\Omega$	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	20	A	
Pulsed diode forward current <sup>a</sup>	$I_{SM}$		-	-	80		
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 20\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	520	780	ns	
Body diode reverse recovery charge	$Q_{rr}$		-	5.3	8.0	$\mu\text{C}$	
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature
- b. Pulse width  $\leq 400\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\text{ }\%$



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

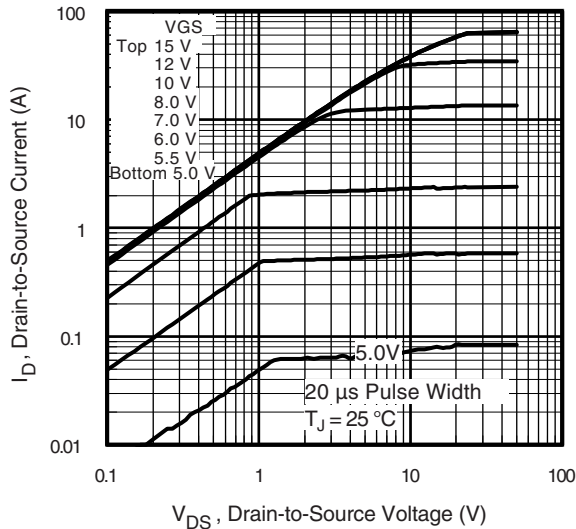


Fig. 1 - Typical Output Characteristics

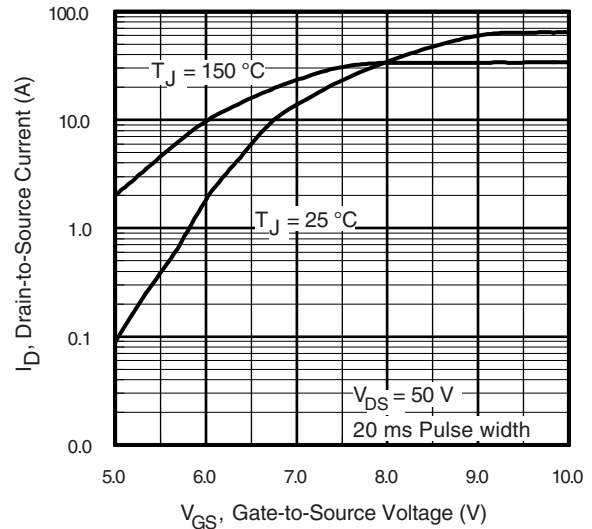


Fig. 3 - Typical Transfer Characteristics

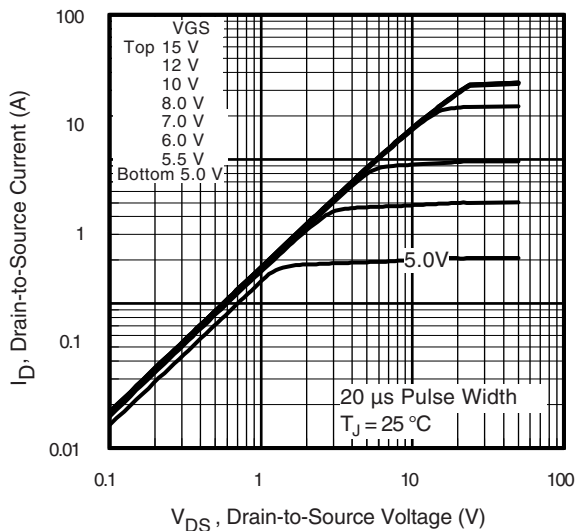


Fig. 2 - Typical Output Characteristics

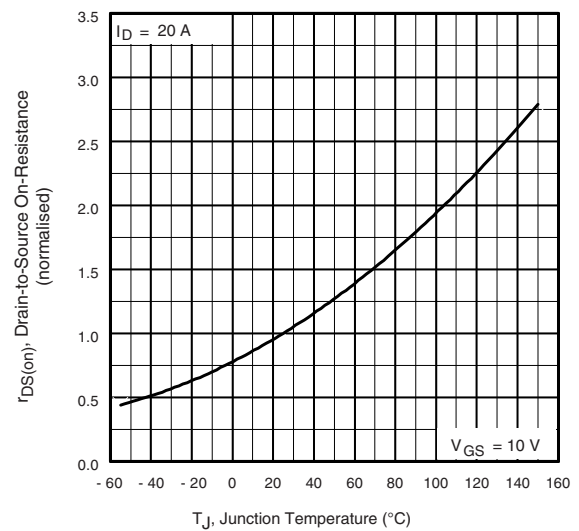


Fig. 4 - Normalized On-Resistance vs. Temperature

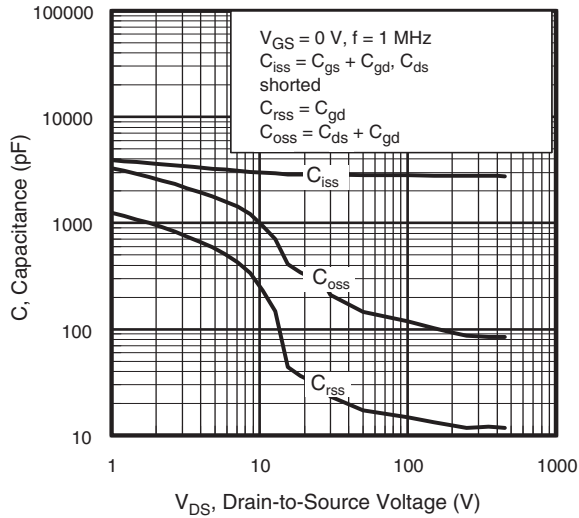


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

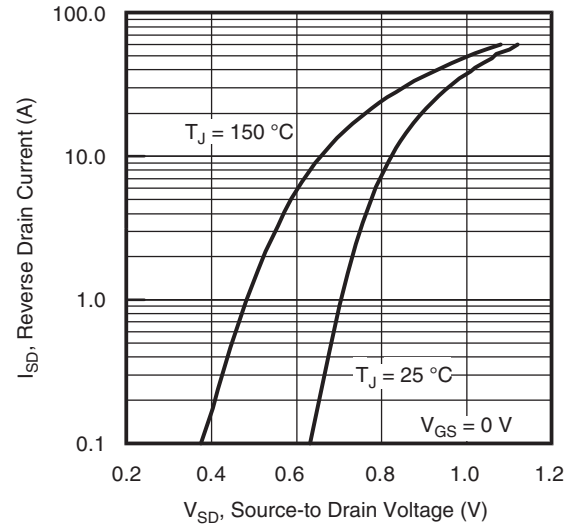


Fig. 7 - Typical Source-Drain Diode Forward Voltage

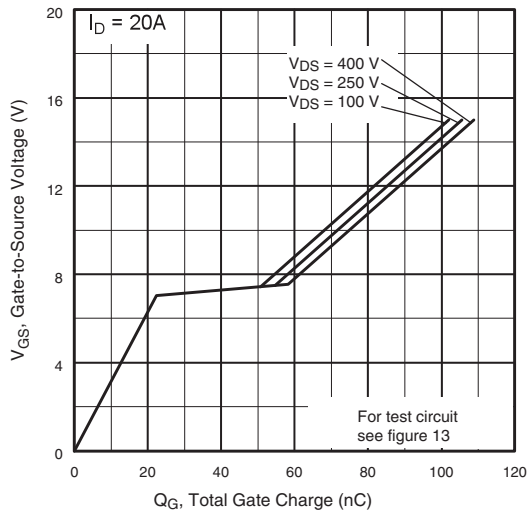


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

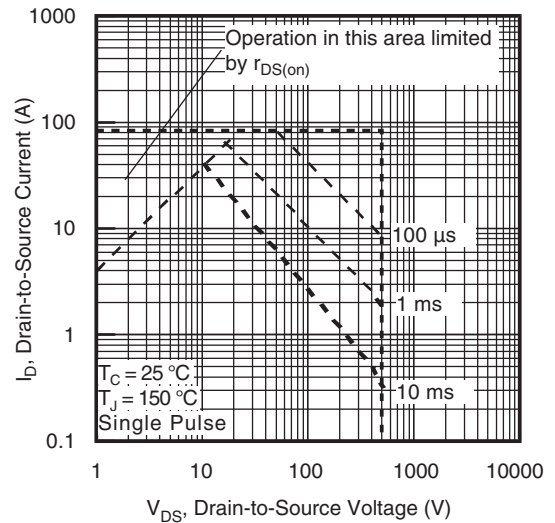


Fig. 8 - Maximum Safe Operating Area

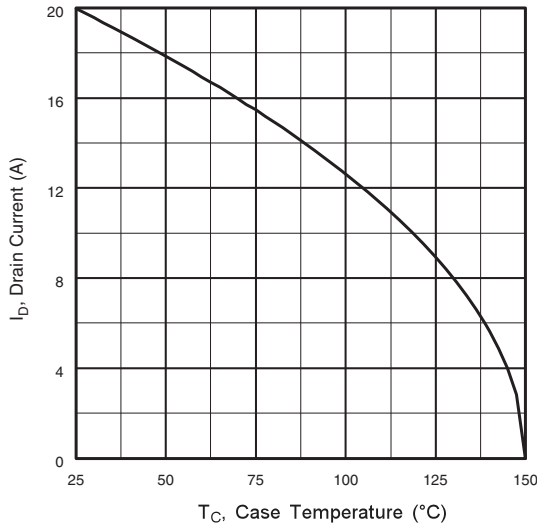


Fig. 9 - Maximum Drain Current vs. Case Temperature

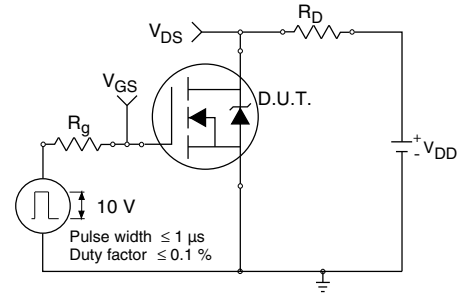


Fig. 10a - Switching Time Test Circuit

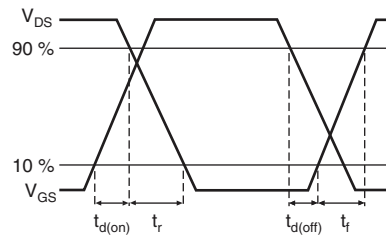


Fig. 10b - Switching Time Waveforms

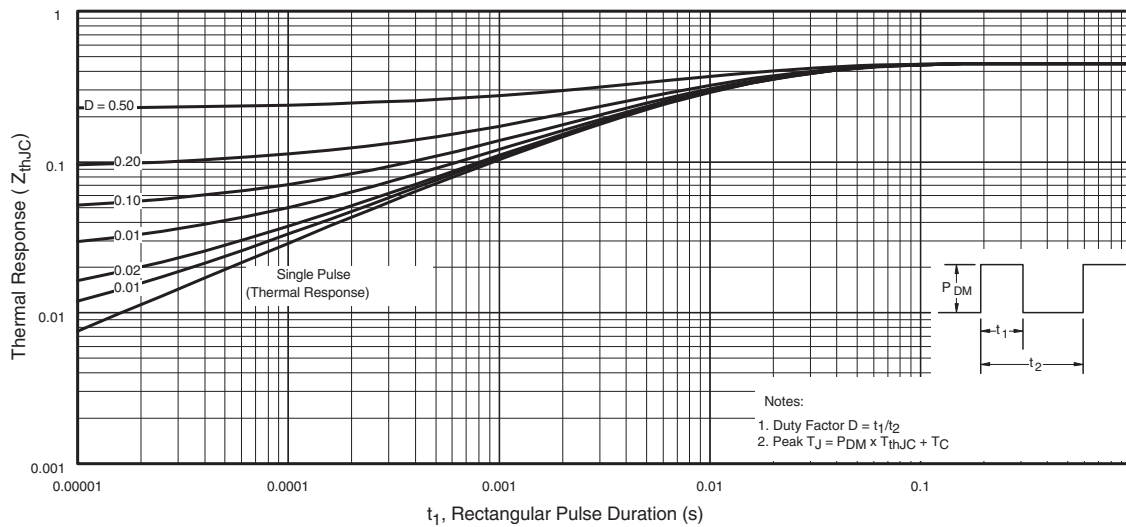


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

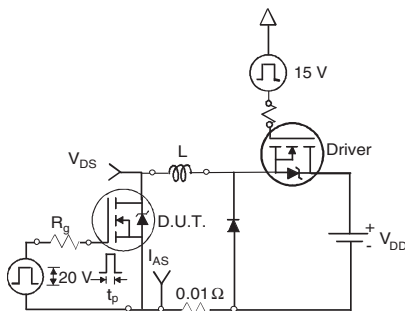


Fig. 12a - Unclamped Inductive Test Circuit

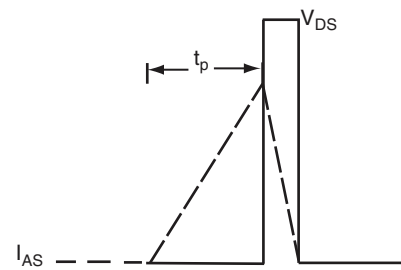


Fig. 12b - Unclamped Inductive Waveforms

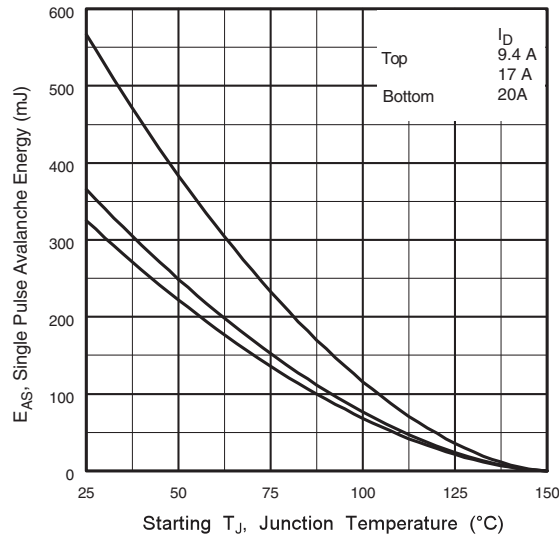


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

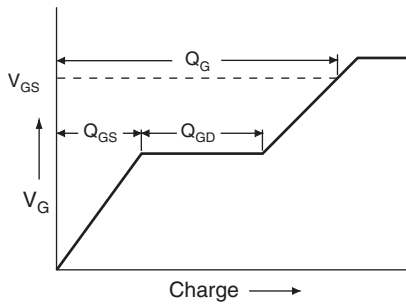


Fig. 13a - Basic Gate Charge Waveform

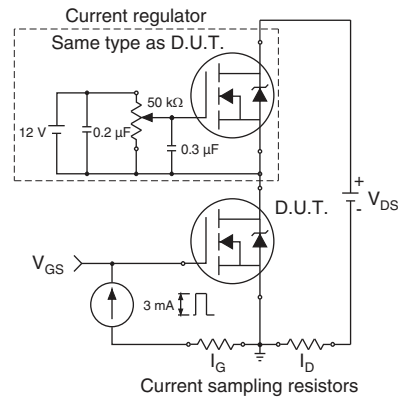
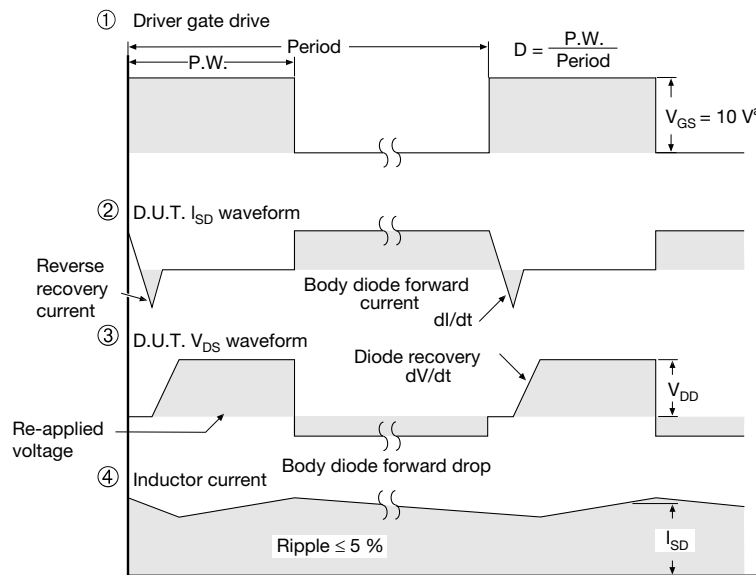
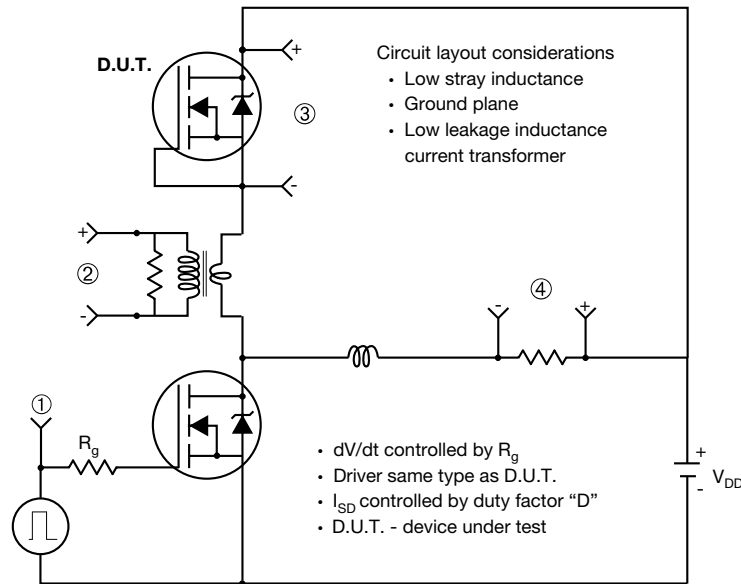


Fig. 13b - Gate Charge Test Circuit

### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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